```
(2777) ("NMOS" and "PMOS" and (transistor with (parti
(3211) ("NMOS" and "PMOS" and (substrate with (parti
(581)  ("NMOS" and "PMOS" and ((silicon adj layer) wit
(3284) ((("NMOS" and "PMOS" and (substrate with (part
(3008) (((("NMOS" and "PMOS" and (substrate with (pa
(951)  ((((("NMOS" and "PMOS" and (substrate with (pa
(92)   (((((("NMOS" and "PMOS" and (substrate with (pa
(80)   ((((((("NMOS" and "PMOS" and (substrate with (p
(15)   (((((((("NMOS" and "PMOS" and (substrate with (
(65)   (((((((("NMOS" and "PMOS" and (substrate with (
(1)    "20020179957"
(0)    20020179957.URPN.
(8)    "5111255"
(8)    ("4558337" | "4590502" | "4686550" | "4800415" |
(7)    5111255.URPN.
(3)    ("4825264" | "5111255" | "5162877").PN.
(8)    ("4558337" | "4590502" | "4686550" | "4800415" |
```

Browse   Queue   Clear

DBs   USPAT; US-PGPUB; EPO; JPO; IBM_TDB   Plurals

Default operator   OR   Highlight all hit terms initially

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(((((((("NMOS" and "PMOS" and (substrate with (partial$4 (etch$4 or
remov$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with
(partial$4 (etch$4 or remov$4)))))) and (method or process)) and
(insulat$4 or dielectric$4)) and (oxidi$3)) and (second adj
transistor)) and (source and drain and gate)) and (second adj
portion)
```

BRS form   IS&R form   Image   Text   HTML

	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C			
1					US 20010052610	20011220	45	Reduced topography DRAM cell fabricated using a	257/296	257/301; 438/243;		Leung, Wingyu et al.	R				
2					US 6140684 A	20001031	14	SRAM cell structure with dielectric	257/368	257/393; 257/903;		Chan, Tsiu Chiu et al.	R				
3					US 5892706 A	19990406	43	Fram, fram card, and card system using the	365/145	365/226; 365/65		Shimizu, Mitsuru et al.	R				
4					US 5841175 A	19981124	48	Semiconductor device in which an increase in	257/392	257/404; 257/E27.06		Sugiura, Souichi et al.	R				
5					US 5831300 A	19981103	61	Semiconductor integrated circuit	257/298	257/300; 257/303;		Tadaki, Yoshitaka et al.	R				
6					US 5798964 A	19980825	43	FRAM, FRAM card, and card system using the	365/145	365/149; 365/226;		Shimizu, Mitsuru et al.	R				
7					US 5683927 A	19971104	9	Method of forming CMOS integrated circuitry	438/231	257/E27.064;		Dennison, Charles H. et al.					
8					US 5674763 A	19971007	48	Method of manufacturing a semiconductor device	438/200	148/DIG.35;		Sugiura, Souichi et al.	R				
9					US 5541870 A	19960730	22	Ferroelectric memory and non-volatile memory	365/145	257/295; 257/E27.10		Mihara, Takashi et al.	R				
10					US 5426315 A	19950620	17	Thin-film transistor having an inlaid	257/66	257/351; 257/411;		Pfiester, James R.	R				
11					US 5334861 A	19940802	15	Semiconductor memory cell	257/67	257/369; 257/69;		Pfiester, James R. et al.	R				

Hic   Details   HTML

Ready   NUM SCRL

3-9-04

L Number	Hits	Search Text	DB	Time stamp
1	21	chan-darin-a.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:13
2	0	chan-darin-a.in. and second adj transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:13
3	14	chan-darin-a.in. and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:14
4	1	(chan-darin-a.in. and transistor) and source and drain and (silicon adj layer)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:14
5	33	(US-6100124-$ or US-5937285-$ or US-5908309-$ or US-5015595-$ or US-5273914-$ or US-4902634-$ or US-4422885-$ or US-4771014-$ or US-4477310-$ or US-4703551-$ or US-6501097-$ or US-4642878-$ or US-4637124-$ or US-6235568-$ or US-6440832-$ or US-5963278-$ or US-5899547-$ or US-6060748-$ or US-5627399-$ or US-6420730-$ or US-5834350-$ or US-5428224-$ or US-5162877-$ or US-5909400-$ or US-6180986-$ or US-6537891-$).did. or (US-5463238-$ or US-5164803-$).did. or (US-20020195623-$ or US-20010016377-$ or US-20020130393-$ or US-20020102780-$ or US-20020171077-$).did.	USPAT; US-PGPUB	2004/03/09 16:15
6	7	((US-6100124-$ or US-5937285-$ or US-5908309-$ or US-5015595-$ or US-5273914-$ or US-4902634-$ or US-4422885-$ or US-4771014-$ or US-4477310-$ or US-4703551-$ or US-6501097-$ or US-4642878-$ or US-4637124-$ or US-6235568-$ or US-6440832-$ or US-5963278-$ or US-5899547-$ or US-6060748-$ or US-5627399-$ or US-6420730-$ or US-5834350-$ or US-5428224-$ or US-5162877-$ or US-5909400-$ or US-6180986-$ or US-6537891-$).did. or (US-5463238-$ or US-5164803-$).did. or (US-20020195623-$ or US-20010016377-$ or US-20020130393-$ or US-20020102780-$ or US-20020171077-$).did.) and (second adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:33
7	39	(second adj transistor) and (diffusivity)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:34

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8	39	((second adj transistor) and (diffusivity)) not (chan-darin-a.in. ((US-6100124-$ or US-5937285-$ or US-5908309-$ or US-5015595-$ or US-5273914-$ or US-4902634-$ or US-4422885-$ or US-4771014-$ or US-4477310-$ or US-4703551-$ or US-6501097-$ or US-4642878-$ or US-4637124-$ or US-6235568-$ or US-6440832-$ or US-5963278-$ or US-5899547-$ or US-6060748-$ or US-5627399-$ or US-6420730-$ or US-5834350-$ or US-5428224-$ or US-5162877-$ or US-5909400-$ or US-6180986-$ or US-6537891-$).did. or (US-5463238-$ or US-5164803-$).did. or (US-20020195623-$ or US-20010016377-$ or US-20020130393-$ or US-20020102780-$ or US-20020171077-$).did.))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:34
9	33	(((second adj transistor) and (diffusivity)) not (chan-darin-a.in. ((US-6100124-$ or US-5937285-$ or US-5908309-$ or US-5015595-$ or US-5273914-$ or US-4902634-$ or US-4422885-$ or US-4771014-$ or US-4477310-$ or US-4703551-$ or US-6501097-$ or US-4642878-$ or US-4637124-$ or US-6235568-$ or US-6440832-$ or US-5963278-$ or US-5899547-$ or US-6060748-$ or US-5627399-$ or US-6420730-$ or US-5834350-$ or US-5428224-$ or US-5162877-$ or US-5909400-$ or US-6180986-$ or US-6537891-$).did. or (US-5463238-$ or US-5164803-$).did. or (US-20020195623-$ or US-20010016377-$ or US-20020130393-$ or US-20020102780-$ or US-20020171077-$).did.))) and (source and drain)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:34
10	17	((((second adj transistor) and (diffusivity)) not (chan-darin-a.in. ((US-6100124-$ or US-5937285-$ or US-5908309-$ or US-5015595-$ or US-5273914-$ or US-4902634-$ or US-4422885-$ or US-4771014-$ or US-4477310-$ or US-4703551-$ or US-6501097-$ or US-4642878-$ or US-4637124-$ or US-6235568-$ or US-6440832-$ or US-5963278-$ or US-5899547-$ or US-6060748-$ or US-5627399-$ or US-6420730-$ or US-5834350-$ or US-5428224-$ or US-5162877-$ or US-5909400-$ or US-6180986-$ or US-6537891-$).did. or (US-5463238-$ or US-5164803-$).did. or (US-20020195623-$ or US-20010016377-$ or US-20020130393-$ or US-20020102780-$ or US-20020171077-$).did.))) and (source and drain)) and (silicon adj layer)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:34
-	5	(("6100124") or ("6153443") or ("6235568") or ("5940319") or ("5937285")).PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/26 11:04
-	9	("5089441" | "5168072" | "5252501" | "5397909" | "5403434" | "5716861" | "5801078" | "5908309" | "6066523").PN.	USPAT	2003/01/30 19:19
-	2	("5273914" | "5290712").PN.	USPAT	2003/01/30 19:21

-	13	("4366613" | "4422885" | "4477310" | "4703551" | "4771014" | "4786609" | "4902634" | "4975718" | "4987089" | "5015595" | "5030582" | "5132234" | "5141890").PN.	USPAT	2003/01/30 19:23
-	1	"6501097"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/30 19:50
-	2	("5403775" | "5872031").PN.	USPAT	2003/01/30 19:58
-	6	5937285.URPN.	USPAT	2003/01/30 19:59
-	2	("5403775" | "5872031").PN.	USPAT	2003/01/30 20:04
-	6	("4530150" | "4562638" | "4590663" | "4599789" | "4637124" | "4642878").PN.	USPAT	2003/01/31 15:49
-	6	("4366613" | "4488351" | "4505024" | "4525920" | "4530150" | "4536944").PN.	USPAT	2003/01/31 15:47
-	58	("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 16:38
-	35	(("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) and thickness	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 15:56
-	35	((("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) and thickness) and (diffus$4 or deplet$4 or dop$4 or ion$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 15:58
-	33	(((("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) and thickness) and (diffus$4 or deplet$4 or dop$4 or ion$4)) and etch$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 15:59
-	33	((((("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) and thickness) and (diffus$4 or deplet$4 or dop$4 or ion$4)) and etch$4) and (method or process)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 16:01
-	10	(((((("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) and thickness) and (diffus$4 or deplet$4 or dop$4 or ion$4)) and etch$4) and (method or process)) and (oxidi$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 16:07
-	0	((((((("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) and thickness) and (diffus$4 or deplet$4 or dop$4 or ion$4)) and etch$4) and (method or process)) and (oxidi$3)) not ((((((("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) and thickness) and (diffus$4 or deplet$4 or dop$4 or ion$4)) and etch$4) and (method or process))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 16:08
-	23	((((((("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) and thickness) and (diffus$4 or deplet$4 or dop$4 or ion$4)) and etch$4) and (method or process)) not ((((((("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) and thickness) and (diffus$4 or deplet$4 or dop$4 or ion$4)) and etch$4) and (method or process)) and (oxidi$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 16:08
-	23	(("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) not ((("NMOS" and "PMOS" and (second adj transistor) and (deep$4 with (source)))) and thickness)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 16:39

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-	82	("4103297" | "4239346" | "4609930" | "4618878" | "4680580" | "4748485" | "4818077" | "4853760" | "4938565" | "4949141" | "4977105" | "4984033" | "4996575" | "5003356" | "5012228" | "5017983" | "5034788" | "5051570" | "5055899" | "5056895" | "5084905" | "5091334" | "5103277" | "5117278" | "5124769" | "5140391" | "5185535" | "5196911" | "5198379" | "5200846" | "5227900" | "5233211" | "5235195" | "5246882" | "5273921" | "5275972" | "5281840" | "5287205" | "5294821" | "5308998" | "5327001" | "5338959" | "5359219" | "5365079" | "5367180" | "5371398" | "5412240" | "5420048" | "5424244" | "5434433" | "5453858" | "5461419" | "5470793" | "5475238" | "5485019" | "5495119" | "5495353" | "5497019" | "5499123" | "5506436" | "5567959" | "5568288" | "5580802" | "5604368" | "5604380" | "5612799" | "5641974" | "5650637" | "5681759" | "5696386" | "5717224" | "5807772" | "5818076" | "5838508" | "5849043" | "5899547" | "5917221" | "5933205" | "5963278" | "6011277" | "6013928" | "6054734").PN.	USPAT	2003/01/31 16:43
-	8	(("4103297" | "4239346" | "4609930" | "4618878" | "4680580" | "4748485" | "4818077" | "4853760" | "4938565" | "4949141" | "4977105" | "4984033" | "4996575" | "5003356" | "5012228" | "5017983" | "5034788" | "5051570" | "5055899" | "5056895" | "5084905" | "5091334" | "5103277" | "5117278" | "5124769" | "5140391" | "5185535" | "5196911" | "5198379" | "5200846" | "5227900" | "5233211" | "5235195" | "5246882" | "5273921" | "5275972" | "5281840" | "5287205" | "5294821" | "5308998" | "5327001" | "5338959" | "5359219" | "5365079" | "5367180" | "5371398" | "5412240" | "5420048" | "5424244" | "5434433" | "5453858" | "5461419" | "5470793" | "5475238" | "5485019" | "5495119" | "5495353" | "5497019" | "5499123" | "5506436" | "5567959" | "5568288" | "5580802" | "5604368" | "5604380" | "5612799" | "5641974" | "5650637" | "5681759" | "5696386" | "5717224" | "5807772" | "5818076" | "5838508" | "5849043" | "5899547" | "5917221" | "5933205" | "5963278" | "6011277" | "6013928" | "6054734").PN.) and (transistor and "PMOS" and "NMOS")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 16:44
-	18084	("NMOS" and "PMOS")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 17:38
-	247	(("NMOS" and "PMOS")) and (partial$4 near3 remov$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 17:39
-	206	((("NMOS" and "PMOS")) and (partial$4 near3 remov$4)) and (source and drain)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 17:40

-	191	(((("NMOS" and "PMOS")) and (partial$4 near3 remov$4)) and (source and drain)) and (insulat$4 or dielectric)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 17:40
-	191	((((("NMOS" and "PMOS")) and (partial$4 near3 remov$4)) and (source and drain)) and (insulat$4 or dielectric)) and (method or process)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 17:41
-	191	(((((("NMOS" and "PMOS")) and (partial$4 near3 remov$4)) and (source and drain)) and (insulat$4 or dielectric)) and (method or process)) and substrate	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 17:42
-	190	((((((("NMOS" and "PMOS")) and (partial$4 near3 remov$4)) and (source and drain)) and (insulat$4 or dielectric)) and (method or process)) and substrate) and (dop$4 or depleti$4 or ion or implant$4 diffus$5)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 17:44
-	172	(((((((("NMOS" and "PMOS")) and (partial$4 near3 remov$4)) and (source and drain)) and (insulat$4 or dielectric)) and (method or process)) and substrate) and (dop$4 or depleti$4 or ion or implant$4 diffus$5)) and (doppant or depletion or implantation or diffusion)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 17:46
-	18	((((((((("NMOS" and "PMOS")) and (partial$4 near3 remov$4)) and (source and drain)) and (insulat$4 or dielectric)) and (method or process)) and substrate) and (dop$4 or depleti$4 or ion or implant$4 diffus$5)) and (doppant or depletion or implantation or diffusion)) and ((second adj region) or (second adj portion))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/31 17:47
-	4	("5097314" | "5461253" | "5627399" | "5754077").PN.	USPAT	2003/01/31 17:52
-	1	6060748.URPN.	USPAT	2003/01/31 17:54
-	2777	("NMOS" and "PMOS" and (transistor with (partial$4 (etch$4 or remov$4))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/03 14:50
-	3211	("NMOS" and "PMOS" and (substrate with (partial$4 (etch$4 or remov$4))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/03 14:52
-	581	("NMOS" and "PMOS" and ((silicon adj layer) with (partial$4 (etch$4 or remov$4))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/03 14:52
-	3284	((("NMOS" and "PMOS" and (substrate with (partial$4 (etch$4 or remov$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial$4 (etch$4 or remov$4)))))) and (method or process)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/03 14:54
-	3008	(((("NMOS" and "PMOS" and (substrate with (partial$4 (etch$4 or remov$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial$4 (etch$4 or remov$4)))))) and (method or process)) and (insulat$4 or dielectric$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/03 14:55
-	951	((((("NMOS" and "PMOS" and (substrate with (partial$4 (etch$4 or remov$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial$4 (etch$4 or remov$4)))))) and (method or process)) and (insulat$4 or dielectric$4)) and (oxidi$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/03 14:55

-	92	`((((((("NMOS" and "PMOS" and (substrate with (partial$4 (etch$4 or remov$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial$4 (etch$4 or remov$4)))))) and (method or process)) and (insulat$4 or dielectric$4)) and (oxidi$3)) and (second adj transistor)`	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/03 14:56
-	80	`(((((((("NMOS" and "PMOS" and (substrate with (partial$4 (etch$4 or remov$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial$4 (etch$4 or remov$4)))))) and (method or process)) and (insulat$4 or dielectric$4)) and (oxidi$3)) and (second adj transistor)) and (source and drain and gate)`	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/03 14:58
-	15	`((((((((("NMOS" and "PMOS" and (substrate with (partial$4 (etch$4 or remov$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial$4 (etch$4 or remov$4)))))) and (method or process)) and (insulat$4 or dielectric$4)) and (oxidi$3)) and (second adj transistor)) and (source and drain and gate)) and (second adj portion)`	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/03 15:13
-	65	`(((((((((("NMOS" and "PMOS" and (substrate with (partial$4 (etch$4 or remov$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial$4 (etch$4 or remov$4)))))) and (method or process)) and (insulat$4 or dielectric$4)) and (oxidi$3)) and (second adj transistor)) and (source and drain and gate)) not ((((((((((("NMOS" and "PMOS" and (substrate with (partial$4 (etch$4 or remov$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial$4 (etch$4 or remov$4)))))) and (method or process)) and (insulat$4 or dielectric$4)) and (oxidi$3)) and (second adj transistor)) and (source and drain and gate)) and (second adj portion))`	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/03 15:13
-	1	`"20020179957"`	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/30 10:02
-	0	`20020179957.URPN.`	USPAT	2003/04/29 17:55
-	8	`"5111255"`	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/30 10:02
-	8	`("4558337" | "4590502" | "4686550" | "4800415" | "4806997" | "4814836" | "4860068" | "4862228").PN.`	USPAT	2003/04/30 10:03
-	7	`5111255.URPN.`	USPAT	2003/04/30 10:04
-	3	`("4825264" | "5111255" | "5162877").PN.`	USPAT	2003/04/30 14:48
-	8	`("4558337" | "4590502" | "4686550" | "4800415" | "4806997" | "4814836" | "4860068" | "4862228").PN.`	USPAT	2003/04/30 14:49
-	7	`5111255.URPN.`	USPAT	2003/04/30 14:50
-	523	`((semiconductor adj layer) with etch$4) and (isolation adj region)`	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:24
-	484	`(((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)`	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 01:44

-	66	((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 01:45
-	59	(((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 01:45
-	40	((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 01:45
-	39	(((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 01:46
-	0	(((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask)) and resist) and antireflect$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 01:47
-	0	(((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask)) and resist) and (anti adj reflect$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 01:47
-	29	((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask)) and resist	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:02
-	14	("4314267" | "4609931" | "4612629" | "4672416" | "4830973" | "4939563" | "4947192" | "5034782" | "5040041" | "5075250" | "5140400" | "5177584" | "5412240" | "5434441").PN.	USPAT	2003/05/05 01:57
-	10	((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask)) not ((((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask)) and resist)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:04
-	127	((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (lower adj (portion or region or section or area))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:10
-	112	(((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (lower adj (portion or region or section or area))) and (insulat$4 adj layer)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:06
-	112	((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (lower adj (portion or region or section or area))) and (insulat$4 adj layer)) and (substrate and etch$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:06
-	0	(((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (lower adj (portion or region or section or area))) and (insulat$4 adj layer)) and (substrate and etch$4)) and (mask and resist and oxidez$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:07

–		26	((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (lower adj (portion or region or section or area))) and (insulat$4 adj layer)) and (substrate and etch$4)) and (mask and resist)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:07
–		21	(((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (lower adj (portion or region or section or area))) and (insulat$4 adj layer)) and (substrate and etch$4)) and (mask and resist)) not ((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:07
–		12	(((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and (lower adj (portion or region or section or area))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:10
–		11	((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and (lower adj (portion or region or section or area))) not ((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (lower adj (portion or region or section or area))) and (insulat$4 adj layer)) and (substrate and etch$4)) and (mask and resist)) not ((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:11
–		11	(((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and (lower adj (portion or region or section or area))) not ((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (lower adj (portion or region or section or area))) and (insulat$4 adj layer)) and (substrate and etch$4)) and (mask and resist)) not ((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask)))) not (((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask)) and resist) and antireflect$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:13
–		523	(((semiconductor adj layer) with etch$4) and (isolation adj region)) and ((semiconductor adj layer) same etch$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:14
–		523	(((semiconductor adj layer) with etch$4) and (isolation adj region)) and ((semiconductor adj layer) with etch$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:14

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-	27	(((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) not ((((((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate)) and transistor) and oxidiz$4) and (mask))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:21
-	4	(((semiconductor adj layer) with etch$4) and (isolation adj region)) and (lower adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:21
-	7	("5623155" | "5729039" | "5973364" | "6191449" | "6288425" | "6348714" | "6414355" | "2002/0048972").PN.	USPAT	2003/05/05 02:22
-	592	substrate and insulat$4 and (isolati$3 adj region) and (second adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:57
-	86	(substrate and insulat$4 and (isolati$3 adj region) and (second adj transistor)) and (mask and resist and oxidiz$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:26
-	85	((substrate and insulat$4 and (isolati$3 adj region) and (second adj transistor)) and (mask and resist and oxidiz$4)) and etch$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:28
-	80	(((substrate and insulat$4 and (isolati$3 adj region) and (second adj transistor)) and (mask and resist and oxidiz$4)) and etch$4) not (((((semiconductor adj layer) with etch$4) and (isolation adj region)) and (insulat$4)) and (insulati$4 adj substrate))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 02:28
-	0	20020125512.URPN.	USPAT	2003/05/05 02:34
-	10	(substrate and insulat$4 and (isolati$3 adj region) and (second adj transistor)) and (lower adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 03:00
-	713	("silicon-on-insulator" or "SOI") and (isolat$4 adj trench)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 03:01
-	3	"6037632"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 10:32
-	7	("4422089" | "5132769" | "5177572" | "5438215" | "5488236" | "5510634" | "5572048").PN.	USPAT	2003/05/05 10:34
-	2	6037632.URPN.	USPAT	2003/05/05 10:36
-	0	("535" and (second adj transistor)) and (fully adj depleted adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 10:41
-	0	("535" and (second adj transistor)) and (partially adj depleted adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 10:42
-	123	("535" and (second adj transistor)) and ("NMOS" and "PMOS")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 10:42
-	11	(("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 10:43

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–	11	(("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 10:47
–	486	"535" and (second adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:04
–	535	((("silicon-on-insulator" or "SOI") and (isolat$4 adj trench)) and transistor and etch$4) and insulat$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:08
–	0	((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) and (isolati$4 adj trench)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:15
–	0	((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) and (isolat$4 adj trench)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:16
–	112	(("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:51
–	0	((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) and (isolat$4 adj trench)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:17
–	112	((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:17
–	0	(((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) and transistor) and (isolat$4 adj trench)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:18
–	0	(((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) and transistor) and (isolati$3 adj trench)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:18
–	0	(((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) and transistor) and (trench)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:18
–	483	(((("silicon-on-insulator" or "SOI") and (isolat$4 adj trench)) and transistor and etch$4) and insulat$3) and (isolati$4 adj trench)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:18
–	65	(((((("silicon-on-insulator" or "SOI") and (isolat$4 adj trench)) and transistor and etch$4) and insulat$3) and (isolati$4 adj trench)) and (("PMOS" and "NMOS") and (isolat$4 adj trench))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:50
–	9	("4090254" | "4276616" | "4677589" | "4933899" | "5027323" | "5038191" | "5060194" | "5757693" | "5761114").PN.	USPAT	2003/05/05 11:36
–	19	5909400.URPN.	USPAT	2003/05/05 11:39
–	2	("5898196" | "5909400").PN.	USPAT	2003/05/05 11:42

-	0	6180986.URPN.		USPAT	2003/05/05 11:43
-	19	5909400.URPN.		USPAT	2003/05/05 11:44
-	112	(((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) and transistor) not ((((((("silicon-on-insulator" or "SOI") and (isolat$4 adj trench)) and transistor and etch$4) and insulat$3) and (isolati$4 adj trench)) and (("PMOS" and "NMOS") and (isolat$4 adj trench)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 11:51
-	112	((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) not ((((((("silicon-on-insulator" or "SOI") and (isolat$4 adj trench)) and transistor and etch$4) and insulat$3) and (isolati$4 adj trench)) and (("PMOS" and "NMOS") and (isolat$4 adj trench)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 12:01
-	20	"5909400"		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 15:17
-	2	("5898196" | "5909400").PN.		USPAT	2003/05/05 12:03
-	2	(("5,909,400") or ("20010045561")).PN.		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 15:17
-	11	"5940691"		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/21 15:00
-	19	"5463238"		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/21 15:01
-	30	"5940691" or "5463238"		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/21 15:01
-	7	("3783052" | "4725875" | "4753896" | "4816893" | "4819052" | "5081062" | "5164803").PN.		USPAT	2003/08/21 15:12
-	3	(("5940691") or ("6110765") or ("5463238")).PN.		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/26 11:05
-	41	en-william-g.in.		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:38
-	10	pellerin-john-g.in.		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:38
-	110	michael-mark-w.in.		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:39
-	0	mark-michael-w.in.		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:39

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-		157	en-william-g.in. pellerin-john-g.in. michael-mark-w.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:39
-		100	(en-william-g.in. pellerin-john-g.in. michael-mark-w.in.) and source and drain	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:39
-		98	((en-william-g.in. pellerin-john-g.in. michael-mark-w.in.) and source and drain) and (second transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:40
-		5	((en-william-g.in. pellerin-john-g.in. michael-mark-w.in.) and source and drain) and (second adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:42
-		10	((en-william-g.in. pellerin-john-g.in. michael-mark-w.in.) and source and drain) and (second adj source)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:42
-		9	(((en-william-g.in. pellerin-john-g.in. michael-mark-w.in.) and source and drain) and (second adj source)) not (((en-william-g.in. pellerin-john-g.in. michael-mark-w.in.) and source and drain) and (second adj transistor))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:13
-		410	(second adj transistor) and (buried adj layer)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:44
-		410	((second adj transistor) and (buried adj layer)) not (en-william-g.in. pellerin-john-g.in. michael-mark-w.in.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:44
-		31	(((second adj transistor) and (buried adj layer)) not (en-william-g.in. pellerin-john-g.in. michael-mark-w.in.)) and (second adj source)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:44
-		33	(US-6440832-$ or US-5963278-$ or US-5899547-$ or US-5937285-$ or US-6100124-$ or US-5908309-$ or US-5273914-$ or US-5015595-$ or US-4477310-$ or US-4902634-$ or US-4703551-$ or US-4771014-$ or US-4422885-$ or US-6501097-$ or US-4637124-$ or US-4642878-$ or US-6235568-$ or US-6060748-$ or US-5627399-$ or US-6420730-$ or US-5834350-$ or US-5428224-$ or US-5162877-$ or US-5909400-$ or US-6180986-$ or US-6537891-$).did. or (US-5463238-$ or US-5164803-$).did. or (US-20020195623-$ or US-20010016377-$ or US-20020130393-$ or US-20020102780-$ or US-20020171077-$).did.	USPAT; US-PGPUB	2003/11/21 15:03
-		20	("3894891" | "4153904" | "4313971" | "5488579" | "5594371" | "5670387" | "5670388" | "5767549" | "5789286" | "5811855" | "5821769" | "5877046" | "5929476" | "5940691" | "5985683" | "5985728" | "6054345" | "6061268" | "6084259" | "6144072").PN.	USPAT	2003/11/21 15:19
-		0	6537891.URPN.	USPAT	2003/11/21 15:21
-		0	6537891.URPN.	USPAT	2003/11/21 15:21